## **3.3 V Automotive Grade M-LVDS Driver Receiver**

#### Description

The NBA3N206S is a 3.3 V supply differential Multipoint Low Voltage (M–LVDS) line Driver and Receiver for automotive applications. NBA3N206S offers the Type 2 receiver threshold at 0.1 V.

The NBA3N206S has Type–2 receivers that detect the bus state with as little as 50 mV of differential input voltage over a common–mode voltage range of -1 V to 3.4 V. Type–2 receivers include an offset threshold to provide a detectable voltage under open–circuit, idle–bus, and other faults conditions.

NBA3N206S supports Simplex or Half Duplex bus configurations.

#### Features

- Low–Voltage Differential 30 Ω to 55 Ω Line Drivers and Receivers for Signaling Rates Up to 200 Mbps
- Type-2 Receivers Provide an Offset (100 mV) Threshold to Detect Open-Circuit and Idle-Bus Conditions
- Controlled Driver Output Voltage Transition Times for Improved Signal Quality
- -1 V to 3.4 V Common–Mode Voltage Range Allows Data Transfer With up to 2 V of Ground Noise
- Bus Pins High Impedance When Disabled or VCC  $\leq 1.5$  V
- M–LVDS Bus Power Up/Down Glitch Free
- Operating range:  $VCC = 3.3 \pm 10\% V(3.0 \text{ to } 3.6 \text{ V})$
- Operation from  $-40^{\circ}$ C to  $+125^{\circ}$ C.
- AEC–Q100 Qualified and PPAP Capable
- These are Pb–Free Devices

#### Applications

- Low-Power High-Speed Short-Reach Alternative to TIA/EIA-485
- Backplane or Cabled Multipoint Data and Clock Transmission
- Cellular Base Stations
- Central–Office Switches
- Network Switches and Routers
- Automotive



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#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 17 of this data sheet.

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Figure 1. Logic Diagram



Table 1. PIN DESCRIPTION

Number	Name	I/O Type	Open Default	Description
1	R	LVCMOS Output		Receiver Output Pin
2	RE	LVCMOS Input	High	Receiver Enable Input Pin (LOW = Active, HIGH = High Z Output)
3	DE	LVCMOS Input	Low	Driver Enable Input Pin (LOW = High Z Output, HIGH=Active)
4	D	LVCMOS Input		Driver Input Pin
5	GND			Ground Supply pin. Pin must be connected to power supply to guarantee proper operation.
6	A	M–LVDS Input /Output		Transceiver True Input /Output Pin
7	В	M–LVDS Input /Output		Transceiver Invert Input /Output Pin
8	VCC			Power Supply pin. Pin must be connected to power supply to guarantee proper operation.

#### **Table 2. DEVICE FUNCTION TABLE**

	Inputs		Output	
	$V_{ID} = V_A - V_B$	RE	R	
	$V_{ID} \ge 150 \text{ mV}$	L	Н	
TYPE 2 Receiver	50 mV < V <sub>ID</sub> < 150 mV	L	?	
ITPE 2 Receiver	$V_{ID} \le 50 \text{ mV}$	L	L	
	Х	Н	Z	
	Х	Open	Z	
	Open	L	L	
	Input	Enable	Output	
	D	DE	A/Y	B/Z
	L	Н	L	Н
DRIVER	Н	Н	Н	L
	Open	Н	L	Н
	Х	Open	Z	Z
	Х	L	Z	Z

H = High, L = Low, Z = High Impedance, X = Don't Care, ? = Indeterminate

#### Table 3. ATTRIBUTES (Note 1)

	Characteristics		Value	
ESD Protection	Human Body Model (JEDEC Standard 22, Method A114–A)	A, B All Pins	±6 kV ±2 kV	
	Machine Model	All Pins	±200 V	
	Charged –Device Model (JEDEC Standard 22, Method C101)	±1500 V		
Moisture Sens	itivity, Indefinite Time Out of Drypack (N	ote 1)	Level 1	
Flammability Rating Oxygen Index		UL-94 code V-0 A 1/8" 28 to 34		
Transistor Count		917 Devices		
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test				

1. For additional information, see Application Note AND8003/D.

#### **Table 4. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	Supply Voltage			$-0.5 \leq V_{CC} \leq 4.0$	V
V <sub>IN</sub>	Input Voltage	D, DE, RE		$-0.5 \leq V_{IN} \leq 4.0$	V
		А, В		$-1.8 \leq V_{IN} \leq 4.0$	1
I <sub>OUT</sub>	Output Voltage	R A, B		$\begin{array}{l} -0.3 \leq I_{OUT} \leq 4.0 \\ -1.8 \leq I_{OUT} \leq 4.0 \end{array}$	V
T <sub>A</sub>	Operating Temperature Range, Industrial			-40 to ≤ +125	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8	190 130	°C/W °C/W
θJC	Thermal Resistance (Junction-to-Case)	(Note 2)	SOIC-8	41 to 44	°C/W
T <sub>sol</sub>	Wave Solder			265	°C
P <sub>D</sub>	Power Dissipation (Continuous)		$T_A = 25^{\circ}C$ $25^{\circ}C < T_A < 125^{\circ}C$ $T_A = 125^{\circ}C$	725 5.8 377	mW mW/°C mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
2. JEDEC standard multilayer board – 2S2P (2 signal, 2 power).

Symbol	Characteristic	Min	Тур	Max	Unit
ICC	Power Supply Current Receiver Disabled Driver Enabled $\overline{RE}$ and DE at V <sub>CC</sub> , R <sub>L</sub> = 50 $\Omega$ , All others open Driver and Receiver Disabled RE at VCC, DE at 0 V, R <sub>L</sub> = No Load, All others open Driver and Receiver Enabled RE at 0 V, DE at V <sub>CC</sub> , R <sub>L</sub> = 50 $\Omega$ , All others open Receiver Enabled Driver Disabled RE at 0 V, DE at 0 V, R <sub>L</sub> = 50 $\Omega$ , All others open		13 1 16	22 4 24 13	mA
VIH	Input HIGH Voltage	2		V <sub>CC</sub>	V
VIL	Input LOW Voltage	GND		0.8	V
VBUS	Voltage at any bus terminal VA, VB, VY or VZ	-1.4		3.8	V
VID	Magnitude of differential input voltage	0.05		V <sub>CC</sub>	
DRIVER					
V <sub>AB</sub>	Differential output voltage magnitude (see Figure 4)	440		690	mV

V <sub>AB</sub>	Differential output voltage magnitude (see Figure 4)	440	690	mV
$\Delta  V_{AB} $	Change in Differential output voltage magnitude between logic states (see Figure 4)	-50	50	mV
V <sub>OS(SS)</sub>	Steady state common mode output voltage (see Figure 5)	0.8	1.2	V
$\Delta V_{OS(SS)}$	Change in Steady state common mode output voltage between logic states (see Figure 5)	-50	50	mV
V <sub>OS(PP)</sub>	Peak-to-peak common-mode output voltage (see Figure 5)		150	mV
V <sub>AOC</sub>	Maximum steady-state open-circuit output voltage (see Figure 9)	0	2.4	V
V <sub>BOC</sub>	Maximum steady-state open-circuit output voltage (see Figure 9)	0	2.4	V
V <sub>P(H)</sub>	Voltage overshoot, low-to-high level output (see Figure 7)		1.2 V <sub>SS</sub>	V
V <sub>P(L)</sub>	Voltage overshoot, high-to-low level output (see Figure 7)	-0.2 V <sub>SS</sub>		V
I <sub>IH</sub>	High–level input current (D, DE) V <sub>IH</sub> = 2 V	0	10	uA
۱ <sub>IL</sub>	Low–level input current (D, DE) V <sub>IL</sub> = 0.8 V	0	10	uA
JI <sub>OS</sub> J	Differential short–circuit output current magnitude (see Figure 6)		24	mA
I <sub>OZ</sub>	High–impedance state output current (driver only) $-1.4 \text{ V} \le (\text{VA or VB}) \le 3.8 \text{ V}$ , other output at 1.2 V	-15	10	uA
I <sub>O(OFF)</sub>	Power–off output current (0 V $\leq$ V <sub>CC</sub> $\leq$ 1.5 V) -1.4 V $\leq$ (VA or VB) $\leq$ 3.8 V, other output at 1.2 V	-10	10	uA

#### RECEIVER

V <sub>IT+</sub>	Positive-going Differential Input voltage Threshold (See Figure 11 & Table 8)				mV
	Туре 2			150	
V <sub>IT-</sub>	Negative-going Differential Input voltage Threshold (See Figure 11 & Table 8)				mV
	Туре 2	50			
V <sub>HYS</sub>	Differential Input Voltage Hysteresis (See Figure 11 and Table 2)				mV
	Туре 2		0		
VOH	High-level output voltage (IOH = -8 mA	2.4			V
VOL	Low-level output voltage (IOL = 8 mA)			0.4	V
I <sub>IH</sub>	RE High-level input current (VIH = 2 V)	-10		0	μΑ
۱ <sub>IL</sub>	RE Low-level input current (VIL = 0.8 V)	-10		0	μΑ
I <sub>OZ</sub>	High-impedance state output current (VO = 0 V of 3.6 V)	-10		15	μΑ
C <sub>A</sub> / C <sub>B</sub>	Input Capacitance VI = 0.4 sin( $30E^6\pi t$ ) + 0.5 V, other outputs at 1.2 V using HP4194A impedance analyzer (or equivalent)		3		pF
C <sub>AB</sub>	Differential Input Capacitance V <sub>AB</sub> = 0.4 sin( $30E^{6}\pi$ t) V, other outputs at 1.2 V using HP4194A impedance analyzer (or equivalent)			2.5	pF
C <sub>A/B</sub>	Input Capacitance Balance, (CA/CB)	99		101	%

			<b>Typ</b> (Note		
Symbol	Characteristic	Min	4)	Мах	Unit
BUS INPU	T AND OUTPUT				
Ι <sub>Α</sub>	Input Current Receiver or Transceiver with Driver Disabled				uA
	$V_{A} = 3.8 \text{ V}, V_{B} = 1.2 \text{ V}$ $V_{A} = 0.0 \text{ V or } 2.4 \text{ V}, V_{B} = 1.2 \text{ V}$ $V_{A} = -1.4 \text{ V}, V_{B} = 1.2 \text{ V}$	0 -20 -32		32 20 0	
Ι <sub>Β</sub>	Input Current Receiver or Transceiver with Driver Disabled				uA
	$V_{B} = 3.8 V, V_{A} = 1.2 V$ $V_{B} = 0.0 V \text{ or } 2.4 V, V_{A} = 1.2 V$ $V_{B} = -1.4 V, V_{A} = 1.2 V$	0 -20 -32		32 20 0	
I <sub>AB</sub>	Differential Input Current Receiver or Transceiver with driver disabled (I <sub>A</sub> –I <sub>B</sub> ) $V_A = V_B$ , -1.4 $\leq V_A \leq 3.8$ V	-4		4	uA
I <sub>A(OFF)</sub>	Input Current Receiver or Transceiver Power Off $0V \le V_{CC} \le 1.5$ and:				uA
	$V_{A} = 3.8 \text{ V}, V_{B} = 1.2 \text{ V}$ $V_{A} = 0.0 \text{ V or } 2.4 \text{ V}, V_{B} = 1.2 \text{ V}$ $V_{A} = -1.4 \text{ V}, V_{B} = 1.2 \text{ V}$	0 -20 -32		32 20 0	
I <sub>B(OFF)</sub>	Input Current Receiver or Transceiver Power Off $0V \le V_{CC} \le 1.5$ and:				uA
	$V_{B} = 3.8 \text{ V}, V_{A} = 1.2 \text{ V}$ $V_{B} = 0.0 \text{ V or } 2.4 \text{ V}, V_{A} = 1.2 \text{ V}$ $V_{B} = -1.4 \text{ V}, V_{A} = 1.2 \text{ V}$	0 -20 -32		32 20 0	
I <sub>AB(OFF)</sub>	Receiver Input or Transceiver Input/Output Power Off Differential Input Current; (I <sub>A</sub> –I <sub>B</sub> )				uA
	$V_{A}$ = $V_{B}$ , 0 $\leq$ $V_{CC}$ $\leq$ 1.5 V, $-1.4$ $\leq$ $V_{A}$ $\leq$ 3.8 V	-4		4	
C <sub>A</sub>	Transceiver Input Capacitance with Driver Disabled VA = 0.4 sin( $30E^6\pi t$ ) + 0.5 V using HP4194A impedance analyzer (or equivalent); V <sub>B</sub> = 1.2 V		5		pF
C <sub>B</sub>	Transceiver Input Capacitance with Driver Disabled V <sub>B</sub> = 0.4 sin( $30E^6\pi t$ ) + 0.5 V using HP4194A impedance analyzer (or equivalent); V <sub>A</sub> = 1.2 V		5		pF
C <sub>AB</sub>	Transceiver Differential Input Capacitance with Driver Disabled VA = 0.4 sin( $30E^6\pi t$ ) + 0.5 V using HP4194A impedance analyzer (or equivalent); V <sub>B</sub> = 1.2 V			3.0	pF
C <sub>A/B</sub>	Transceiver Input Capacitance Balance with Driver Disabled, (CA/CB)	99		101	%

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

See Figure 3. DC Measurements reference.
 Typ value at 25°C and 3.3 VCC supply voltage.

#### Table 6. DRIVER AC CHARACTERISTICS VCC = $3.3 \pm 10\%$ V( 3.0 to 3.6 V), GND = 0 V, T<sub>A</sub> = $-40^{\circ}$ C to $+125^{\circ}$ C (Note 5)

Symbol	Characteristic	Min	Тур	Max	Unit
t <sub>PLH</sub> / t <sub>PHL</sub>	Propagation Delay (See Figure 7)	1.0	1.5	2.4	ns
t <sub>PHZ</sub> / t <sub>PLZ</sub>	Disable Time HIGH or LOW state to High Impedance (See Figure 8)			7	ns
t <sub>PZH</sub> / t <sub>PZL</sub>	Enable Time High Impedance to HIGH or LOW state (See Figure 8)			7	ns
t <sub>SK(P)</sub>	Pulse Skew ( t <sub>PLH</sub> – t <sub>PHL</sub>  ) (See Figure 7)		0	150	ps
t <sub>SK(PP)</sub>	Device to Device Skew similar path and conditions (See Figure 7)			1	ns
t <sub>JIT(PER)</sub>	Period Jitter RMS, 100 MHz (Source tr/tf 0.5 ns, 10 and 90 % points, 30k samples. Source jitter de–embedded from Output values ) (See Figure 10)		2	3.5	ps
t <sub>JIT(PP)</sub>	Peak-to-peak Jitter, 200 Mbps 2 <sup>15</sup> –1 PRBS (Source tr/tf 0.5 ns, 10 and 90% points, 100k samples. Source jitter de-embedded from Output values) (See Figure 10)		30	150	ps
tr / tf	Differential Output rise and fall times (See Figure 7)	0.9		1.6	ns

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

5. Typ value at 25°C and 3.3  $V_{CC}$  supply voltage.

Symbol	Characteristic	Min	Тур	Max	Unit
t <sub>PLH</sub> / t <sub>PHL</sub>	Propagation Delay (See Figure 12)	2	4	6	ns
t <sub>PHZ</sub> / t <sub>PLZ</sub>	Disable Time HIGH or LOW state to High Impedance (See Figure 13)			10	ns
t <sub>PZH</sub> / t <sub>PZL</sub>	Enable Time High Impedance to HIGH or LOW state (See Figure 13)			18	ns
t <sub>SK(P)</sub>	Pulse Skew ( t <sub>PLH</sub> – t <sub>PHL</sub>  ) (See Figure 14) $C_L$ = 5 pF Type 2		300	500	ps
t <sub>SK(PP)</sub>	Device to Device Skew similar path and conditions (See Figure 12) $C_L = 5 \text{ pF}$			1	ns
t <sub>JIT(PER)</sub>	Period Jitter RMS, 100 MHz (Source: VID = 200 mV <sub>pp</sub> , VID = 400 mV <sub>pp</sub> , V <sub>CM</sub> =1 V, tr/tf 0.5 ns, 10 and 90 % points, 30k samples. Source jitter de–embedded from Output values ) (See Figure 14)		4	8	ps
t <sub>JIT(PP)</sub>	Peak-to-peak Jitter, 200 Mbps 2 <sup>15</sup> -1 PRBS (Source tr/tf 0.5 ns, 10% and 90% points, 100k samples. Source jitter de-embedded from Output values) (See Figure 14)				ps
	Туре 2		450	900	
tr / tf	Differential Output rise and fall times (See Figure 14) $C_L = 15  pF$	1		2.3	ns

6. Typ value at 25°C and 3.3 VCC supply voltage. .







A. All resistors are 1% tolerance.

Figure 4. Differential Output Voltage Test Circuit



A. All input pulses are supplied by a generator having the following characteristics: tr or tr  $\leq$  1 ns, pulse frequency = 500 kHz, duty cycle = 50 ± 5%.

B. C1, C2 and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20% tolerance.

C. R1 and R2 are metal film, surface mount, 1% tolerance, and located within 2 cm of the D.U.T.

D. The measurement of VOs(PP) is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

#### Figure 5. Test Circuit and Definitions for the Driver Common–Mode Output Voltage



Figure 6. Driver Short-Circuit Test Circuit



A. All input pulses are supplied by a generator having the following characteristics: tr or tr $\leq$  1 ns, frequency = 500 kHz, duty cycle = 50 ±5%.

B. C1, C2, and C3 include instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20%.

C. R1 is a metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.

D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

#### Figure 7. Driver Test Circuit, Timing, and Voltage Definitions for the Differential Output Signal



A. All input pulses are supplied by a generator having the following characteristics: tr or tr $\leq$  1 ns, frequency = 500 kHz, duty cycle = 50 ±5%.

B. C1, C2, C3, and C4 includes instrumentation and fixture capacitance within 2 cm of the D.U.T. and are 20%.

C. R1 and R2 are metal film, surface mount, and 1% tolerance and located within 2 cm of the D.U.T.

D. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

#### Figure 8. Driver Enable and Disable Time Circuit and Definitions



Figure 9. Maximum Steady State Output Voltage



A. All input pulses are supplied by an Agilent 8304A Stimulus System.

B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software

C. Period jitter is measured using a 100 MHz 50  $\pm 1\%$  duty cycle clock input.

D. Peak-to-peak jitter is measured using a 200 Mbps 215-1 PRBS input.

#### Figure 10. Driver Jitter Measurement Waveforms



Figure 11. Receiver Voltage and Current Definitions



A. All input pulses are supplied by a generator having the following characteristics: tr or tr  $\leq$  1 ns, frequency = 50 MHz, duty cycle = 50 ±5%. CL is a combination of a 20%-tolerance, low-loss ceramic, surface-mount capacitor and fixture capacitance within 2 cm of the D.U.T.

B. The measurement is made on test equipment with a -3 dB bandwidth of at least 1 GHz.

#### Figure 12. Receiver Timing Test Circuit and Waveforms



A. All input pulses are supplied by a generator having the following characteristics: tr or tf  $\leq$  1 ns, frequency = 500 kHz, duty cycle = 50  $\pm$ 5%.

B. RL is 1% tolerance, metal film, surface mount, and located within 2 cm of the D.U.T.

C. CL is the instrumentation and fixture capacitance within 2 cm of the DUT and 20%.

#### Figure 13. Receiver Enable/Disable Time Test Circuit and Waveforms



A. All input pulses are supplied by an Agilent 8304A Stimulus System.

B. The measurement is made on a TEK TDS6604 running TDSJIT3 application software

C. Period jitter is measured using a 100 MHz 50  $\pm$ 1% duty cycle clock input.

D. Peak-to-peak jitter is measured using a 200 Mbps 2<sup>15</sup>-1 PRBS input.

#### Figure 14. Receiver Jitter Measurement Waveforms

#### Table 8. TYPE-2 RECEIVER INPUT THRESHOLD TEST VOLTAGES

Applied Voltages		Resulting Differential Input Voltage	Resulting Common– Mode Input Voltage	Receiver Output
VIA	VIB	VID	VIC	(Note )
2.400	0.000	2.400	1.200	Н
0.000	2.400	-2.400	1.200	L
3.800	3.650	0.150	3.725	Н
3.800	3.750	0.050	3.775	L
-1.250	-1.400	0.150	-1.325	Н
-1.350	-1.400	0.050	-1.375	L

H = high level, L = low level, output state assumes receiver is enabled ( $\overline{RE} = L$ )



Figure 15. Equivalent Input and Output Schematic Diagrams

#### **APPLICATION INFORMATION**

#### **Receiver Input Threshold (Failsafe)**

The MLVDS standard defines a type 1 and type 2 receiver. Type 1 receivers include no provisions for failsafe and have their differential input voltage thresholds near zero volts. Type 2 receivers have their differential input voltage thresholds offset from zero volts to detect the absence of a voltage difference. The impact to receiver output by the offset input can be seen in Table 9 and Figure 16.

#### Table 9. RECEIVER INPUT VOLTAGE THRESHOLD REQUIREMENTS

Receiver Type	Output Low	Output High	
Type 1	$-2.4 \text{ V} \leq \text{VID} \leq -0.05 \text{ V}$	$0.05 \text{ V} \leq \text{VID} \leq 2.4 \text{ V}$	
Type 2	$-2.4 \text{ V} \le \text{VID} \le 0.05 \text{ V}$	$0.15 \text{ V} \leq \text{VID} \leq 2.4 \text{ V}$	



#### -100

Figure 16. Receiver Differential Input Voltage Showing Transition Regions by Type

#### LIVE INSERTION/GLITCH-FREE POWER UP/DOWN

The NBA3N206S provides a glitch–free power up/down feature that prevents the M–LVDS outputs of the device from turning on during a power up or power down event. This is especially important in live insertion applications, when a device is physically connected to an M–LVDS multipoint bus and  $V_{CC}$  is ramping.

While the M–LVDS interface for these devices is glitch free on power up/down, the receiver output structure is not.

Figure 17 shows the performance of the receiver output pin, R (CHANNEL 2), as  $V_{CC}$  (CHANNEL 1) is ramped. The glitch on the R pin is independent of the RE voltage. Any complications or issues from this glitch are easily resolved in power sequencing or system requirements that suspend operation until  $V_{CC}$  has reached a steady state value.



Figure 17. M-LVDS Receiver Output: VCC (CHANNEL 1), R Pin (CHANNEL 2)

**Simplex Theory Configurations:** Data flow is unidirectional and Point–to–Point from one Driver to one Receiver. NBA3N206S devices provide a high signal current allowing long drive runs and high noise immunity. Single terminated interconnects yield high amplitude levels.



Figure 18. Point-to-Point Simplex Single Termination

**Simplex Multidrop Theory Configurations**: Data flow is unidirectional from one Driver with one or more Receivers Multiple boards required. Single terminated interconnects yield high amplitude levels. Parallel terminated interconnects yield typical MLVDS amplitude levels and Parallel terminated interconnects yield typical MLVDS amplitude levels and minimizes reflections. See Figures 18 and 19. A NBA3N206S can be used as the driver or as a receiver.



Figure 19. Parallel–Terminated Simplex

minimizes reflections. On the Evaluation Test Board, Headers P1, P2, and P3 may be used as need to interconnect transceivers to a each other or a bus. See Figures 20 and 21. A NBA3N206S can be used as the driver or as a receiver.



Figure 20. Multidrop or Distributed Simplex with Single Termination



Figure 21. Multidrop or Distributed Simplex with Double Termination

Half Duplex Multinode Multipoint Theory Configurations: Data flow is unidirectional and selected from one of multiple possible Drivers to multiple Receivers. One "Two Node" multipoint connection can be accomplished with a single evaluation test board. More than Two Nodes requires multiple evaluation test boards. Parallel terminated interconnects yield typical MLVDS amplitude levels and minimizes reflections. Parallel terminated interconnects yield typical LMVDS amplitude levels and minimizes reflections. On the Test Board, Headers P1, P2, and P3 may be used as need to interconnect transceivers to each other or a bus. See Figure 22. A NBA3N206SDG can be used as the driver or as a receiver.



Figure 22. Multinode Multipoint Half Duplex (requires Double Termination)

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Figure 23.

#### **ORDERING INFORMATION**

Device	Receiver	Pin 1 Quadrant	Package	Shipping <sup>†</sup>
NBA3N206SDG	Туре 2	Q1	SOIC - 8 (Pb-Free)	98 Units / Rail
NBA3N206SDR2G	Type 2	Q1	SOIC – 8 (Pb–Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### STYLES ON PAGE 2

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#### SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

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7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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COLLECTOR, #1

COLLECTOR, #1

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